





#### **60V NPN DARLINGTON TRANSISTOR IN SOT23**

### **Description**

This Darlington Transistor is designed to meet the stringent requirements of automotive applications.

#### **Features**

- BVCEO > 60V
- Darlington Transistor hFE > 10k @ 100mA for High Gain
- Ic = 500mA High Continuous Collector Current
- Complementary Darlington PNP Type: BCV46Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BCV47Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

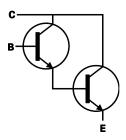
https://www.diodes.com/quality/product-definitions/

## **Mechanical Data**

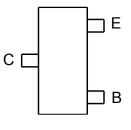
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (Approximate)







Device Symbol



Top View Pinout

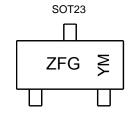
### **Ordering Information** (Note 4)

Orderable Part Number	Number Package Marking Reel Size (inches)		Tape Width (mm)	Packing		
Orderable Fait Number	Fackage	Warking	Reel Size (Illiches)	rape widin (ililii)	Qty.	Carrier
BCV47QTA	SOT23	ZFG	7	8	3,000	Reel
BCV47QTC	SOT23	ZFG	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



ZFG = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  or  $\underline{Y}$  = Year (ex: M = 2025) M or  $\overline{M} = \overline{M}$  onth (ex: 9 = September)

#### Date Code Key

Year	2017	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	Е	1	М	N	Р	R	S	Т	U	V	W	Х
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

1 of 6 BCV47Q February 2025 © 2025 Copyright Diodes Incorporated. All Rights Reserved.



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	80	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	VEBO	10	V
Continuous Collector Current	Ic	500	mA
Peak Pulse Current	Ісм	800	mA
Base Current	lв	100	mA

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Dower Dissination	(Note 5)	D-	310	m\\/	
Power Dissipation	(Note 6)	P <sub>D</sub>	350	mW	
Thermal Desistance Investiga to Archivet	(Note 5)	6	403	90/11/	
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	°C/W	
Thermal Resistance, Junction to Leads (Note 7)		R <sub>0</sub> JL	350	°C/W	
Operating and Storage Temperature Range	•	TJ, TSTG	-55 to +150	°C	

# ESD Ratings (Note 8)

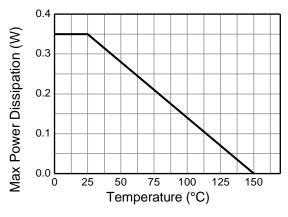
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single-sided 1oz copper in still air condition; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm FR4 PCB.
  7. Thermal resistance from junction to solder-point (at the end of the leads).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Thermal Characteristics and Derating Information (@TA = +25°C, unless otherwise specified.)



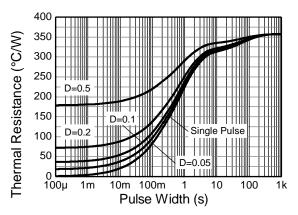


Figure 1. Derating Curve

Figure 2. Transient Thermal Impedance

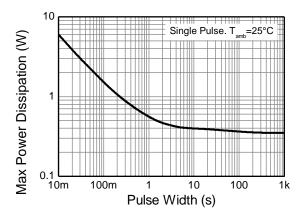


Figure 3. Pulse Power Dissipation

#### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	80	_	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	60	_	_	V	I <sub>CEO</sub> = 10mA
Emitter-Base Breakdown Voltage	ВУЕВО	10	_	_	V	I <sub>EBO</sub> = 10μA
Collector Cutoff Current	Ісво	_	< 1	100	nA	V <sub>CB</sub> = 60V
Collector Cutoff Current	ICBO	_		10	μΑ	$V_{CB} = 60V, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	IEBO	_	< 1	100	nA	V <sub>EB</sub> = 4V
ON CHARACTERISTICS (Note 9)						
Static Forward Current Transfer Ratio	hFE	2,000 4,000 10,000 2,000	_	_	_	I <sub>C</sub> = 100µA, V <sub>CE</sub> = 1V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V I <sub>C</sub> = 500mA, V <sub>CE</sub> = 5V
Collector-Emitter Saturation Voltage	VCE(sat)	_	_	1.0	V	Ic = 100mA, I <sub>B</sub> = 0.1mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	1.5	V	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0.1mA
SMALL-SIGNAL CHARACTERISTICS (Note 9)	SMALL-SIGNAL CHARACTERISTICS (Note 9)					
Transition Frequency	fτ	_	170		MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5V f = 20MHz
Output Capacitance	Cobo	_	3.5	_	pF	V <sub>CB</sub> = 10V, f = 1MHz

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

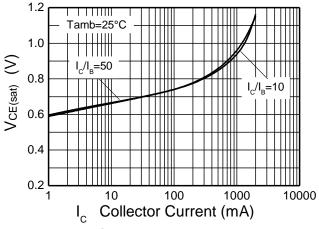


Figure 4. VCE(sat) vs. Ic

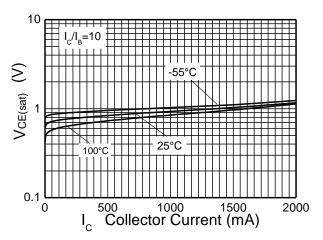


Figure 5.  $V_{\text{CE(sat)}}$  vs.  $I_{\text{C}}$ 

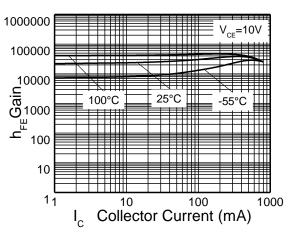


Figure 6. hFE vs. Ic

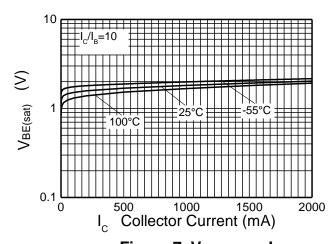


Figure 7. VBE(sat) vs. Ic

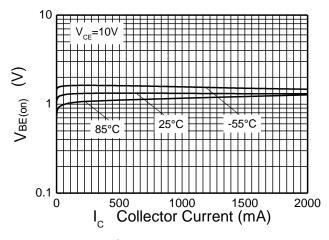


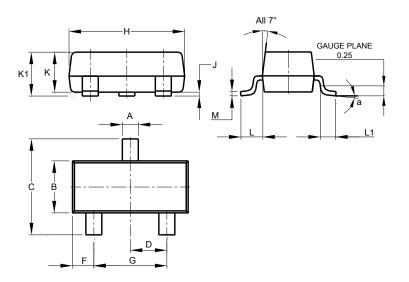
Figure 8. V<sub>BE(on)</sub> vs. I<sub>C</sub>



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

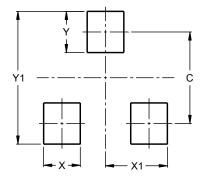


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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